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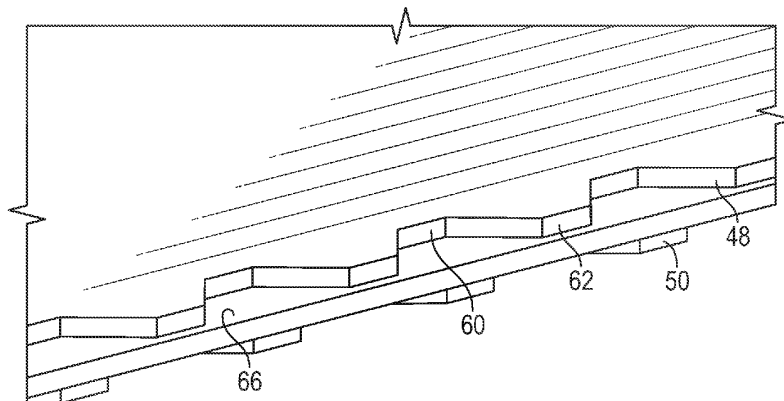


FIG. 6

(57) Abstract: Implementations of a substrate may include an electrically insulative layer (18) having a first largest planar side (26) and a second largest planar side (24) opposing the first largest planar side (26); a first electrically conductive layer (20) coupled to the first largest planar side (26) and including a first scalloped edge (28) having a first pattern; and a second electrically conductive layer (22) coupled to the second largest planar side (24) and including a second scalloped edge (36) having a second pattern. The first pattern and the second pattern may alternate along at least one edge of the first largest planar side (26) and at least one edge of the second largest planar side (24), respectively.

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